

LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)				ATTY. DOCKET NO. Y0996-118X		SERIAL NO.			
				APPLICANT: Kevin K. Chan et al.					
				FILING DATE: HEREWITH		GROUP:			
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Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date			
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AK	A. Acovic et al., "Novel Gate Process for 0.1 Micron MOSFETs",								
AK	IBM Technical Disclosure Bulletin, Vol. 36, No. 11, November 1993.								
	AS								
	AT								
EXAMINER <i>Douglas K. One</i>				DATE CONSIDERED <i>10/8/04</i>					
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